





#### NPN SURFACE MOUNT TRANSISTOR

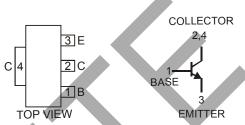
#### **Features**

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (DCX69)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

#### **Mechanical Data**

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.072 grams (approximate)





Schematic and Pin Configuration

### Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	25	V
Collector-Emitter Voltage	V <sub>CEO</sub>	20	V
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	V
Collector Current	Ic	1.0	A
Peak Pulse Current	Ісм	2.0	A

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T <sub>A</sub> = 25°C	P <sub>D</sub>	1	W
Thermal Resistance, Junction to Ambient Air (Note 3) @T <sub>A</sub> = 25°C	$R_{ heta JA}$	125	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

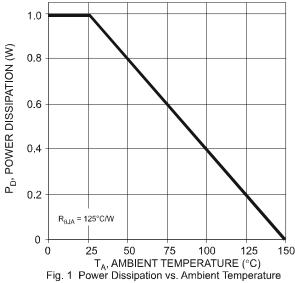
### Electrical Characteristics @TA = 25°C unless otherwise specified

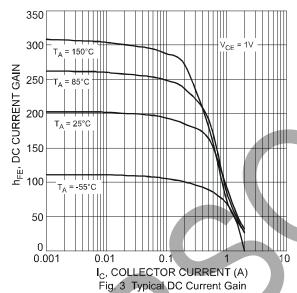
Characteristic		Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS (Note 4)							
Collector-Base Breakdown Voltage		V <sub>(BR)CBO</sub>	25	_	_	V	$I_C = 100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	20	_	_	V	$I_C = 10mA, I_B = 0$
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	5.0	_	_	V	$I_E = 100 \mu A, I_C = 0$
Collector-Base Cutoff Current		I <sub>CBO</sub>	_	_	0.1 10	μА	$V_{CB} = 25V, I_E = 0$ $V_{CB} = 25V, I_E = 0, T_A = 150$ °C
Emitter-Base Cutoff Current		I <sub>EBO</sub>	_	_	10	μΑ	$V_{EB} = 5.0V, I_C = 0$
ON CHARACTERISTICS (Note 4)							
	OCX68-25	h <sub>FE</sub>	50 60		_	<u> </u>	$V_{CE} = 10V, I_{C} = 5.0 \text{mA}$ $V_{CE} = 1.0V, I_{C} = 1.0 \text{A}$
DC Current Gain	DCX68		85	_	375		V <sub>CE</sub> = 1.0V, I <sub>C</sub> = 500mA
	DCX68-25		160		375		$V_{CE} = 1.0V, I_{C} = 500mA$
Collector-Emitter Saturation Voltage		V <sub>CE(SAT)</sub>	_		0.5	V	$I_C = 1.0A$ , $I_B = 100mA$
Base-Emitter Turn-On Voltage		$V_{BE(ON)}$	_	_	1.0	V	I <sub>C</sub> = 1.0A, V <sub>CE</sub> = 1.0V
SMALL SIGNAL CHARACTERISTICS							
Current Gain-Bandwidth Product		f <sub>T</sub>	_	330	_	MHz	$V_{CE} = 5.0V, I_{C} = 100mA,$ f = 100MHz
Output Capacitance		$C_{obo}$	_	_	25	pF	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$

Notes: 1. No purposefully added lead.

- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
- 3. Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 4. Measured under pulsed conditions. Pulse width =  $300\mu$ s. Duty cycle  $\le 2\%$ .







vs. Collector Current (DCP68)

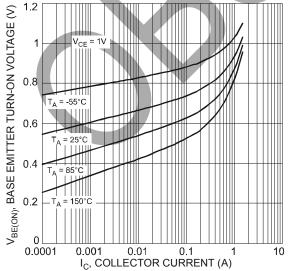
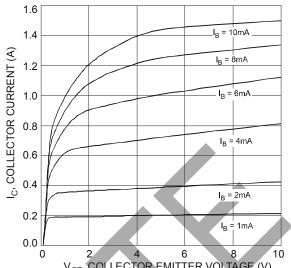


Fig. 5 Typical Base Emitter Turn-On Voltage vs. Collector Current



V<sub>CE</sub>, COLLECTOR EMITTER VOLTAGE (V) Fig. 2 Typical Collector Current vs. Collector Emitter Voltage

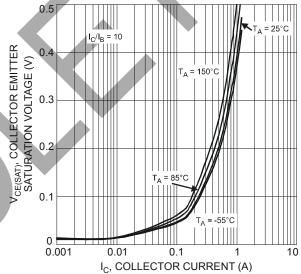


Fig. 4 Typical Collector Emitter Saturation Voltage vs. Collector Current

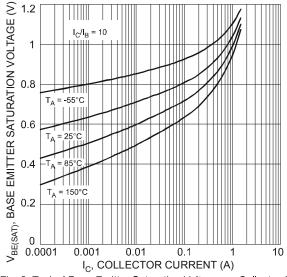
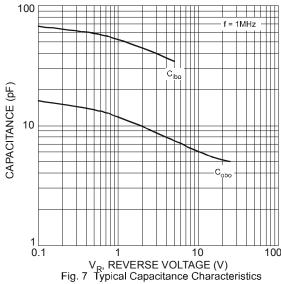
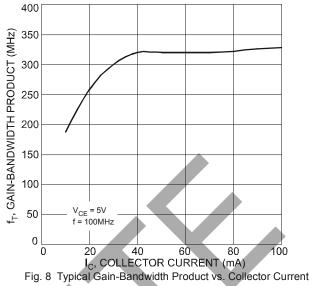


Fig. 6 Typical Base Emitter Saturation Voltage vs. Collector Current





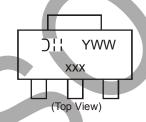


### **Ordering Information** (Note 5)

Device	Packaging	Shipping	
DCX68-13	SOT89-3L	2500/Tape & Reel	
DCX68-25-13	SOT89-3L	2500/Tape & Reel	

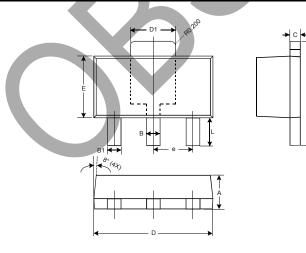
5. For packaging details, go to our website at http://www.diodes.com/ap02007.pdf.

## **Marking Information**



xxx = Product Type Marking Code: N12 = DCX68 N12-25 = DCX68-25 YWW = Date Code Marking Y = Last digit of year ex: 7 = 2007 WW = Week code 01 - 52

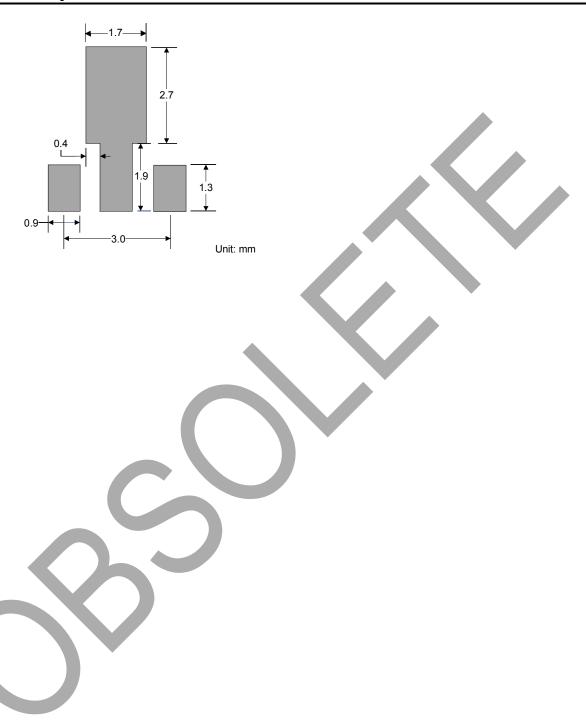
## **Package Outline Dimensions**



SOT89-3L					
Dim	Min	Max	Тур		
Α	1.40	1.60	1.50		
В	0.45	0.55	0.50		
B1	0.37	0.47	0.42		
С	0.35	0.43	0.38		
D	4.40	4.60	4.50		
D1	1.50	1.70	1.60		
E	2.40	2.60	2.50		
е	_	_	1.50		
H	3.95	4.25	4.10		
L	0.90	1.20	1.05		
All Dimensions in mm					



# **Suggested Pad Layout**





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